2.5V Drive Nch+Nch MOS FET QS6K1

Structure

Silicon N-channel MOS FET

Features

1) Low on-resistance.

- 2) Built-in G-S Protection Diode.
- 3) Small and Surface Mount Package (TSMT6).

Application

Power switching, DC / DC converter.

Packaging specifications

	Package	Taping
Туре	Code	TR
	Basic ordering unit (pieces)	3000
QS6K1		0

●Absolute maximum ratings (Ta=25°C)

<It is the same ratings for the Tr1 and Tr2>

Parameter		Symbol	Limits	Unit
Drain-source voltage		VDSS	30	V
Gate-source voltage		Vgss	12	V
Dualia aurorat	Continuous	ID	±1.0	A
Drain current	Pulsed	I _{DP} *1	±4.0	A
Source current	Continuous	ls	0.8	А
(Body diode)	Pulsed	Isp *1	4.0	A
Total power dissipation (Tc=25°C)		Pp *2	1.25	W / TOTAL
		PD -	0.9	W / ELEMENT
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

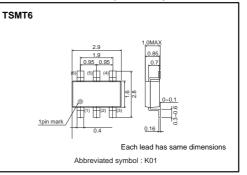
*1 Pw≤10µs, Duty cycle≤1% *2 Mounted on a ceramic board

•Thermal resistance

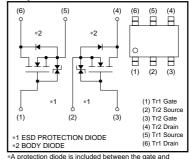
Parameter	Symbol	Limits	Unit
Channel to ambient	Rth (ch-a)*	100	°C / W / TOTAL
	Rtn (cn-a)	139	°C / W / ELEMENT

* Mounted on a ceramic board

•External dimensions (Unit : mm)



•Equivalent circuit



A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

Transistors

●Electrical characteristics (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	lgss	-	-	10	μΑ	Vgs=12V, Vds=0V
Drain-source breakdown voltage	V(BR) DSS	30	-	_	V	I _D =1mA, V _{GS} =0V
Zero gate voltage drain current	IDSS	-	_	1	μΑ	V _{DS} =30V, V _{GS} =0V
Gate threshold voltage	VGS (th)	0.5	_	1.5	V	V _{DS} =10V, I _D =1mA
		-	170	238		I _D =1.0A, V _{GS} =4.5V
Static drain-source on-state resistance	RDS (on)*	-	180	252	mΩ	I _D =1.0A, V _{GS} =4.0V
resistance		-	260	364		I _D =1.0A, V _{GS} =2.5V
Forward transfer admittance	Y _{fs} *	1.0	_	_	S	I _D =1.0A, V _{DS} =10V
Input capacitance	Ciss	-	77	_	pF	V _{DS} =10V
Output capacitance	Coss	-	25	_	рF	V _{GS} =0V
Reverse transfer capacitance	Crss	_	15	-	pF	f=1MHz
Turn-on delay time	t _{d (on)} *	-	7	_	ns	I _D =500mA, V _{DD} ≒15V
Rise time	tr *	-	7	-	ns	V _{GS} =4.5V
Turn-off delay time	td (off) *	-	15	-	ns	RL=30.0Ω
Fall time	t _f *	-	6	-	ns	R _G =10Ω
Total gate charge	Qg *	-	1.7	2.4	nC	V _{DD} ≒15V
Gate-source charge	Q _{gs} *	-	0.4	-	nC	V _{GS} =4.5V
Gate-drain charge	Q _{gd} *	-	0.4	_	nC	I _D =1.0A

*Pulsed

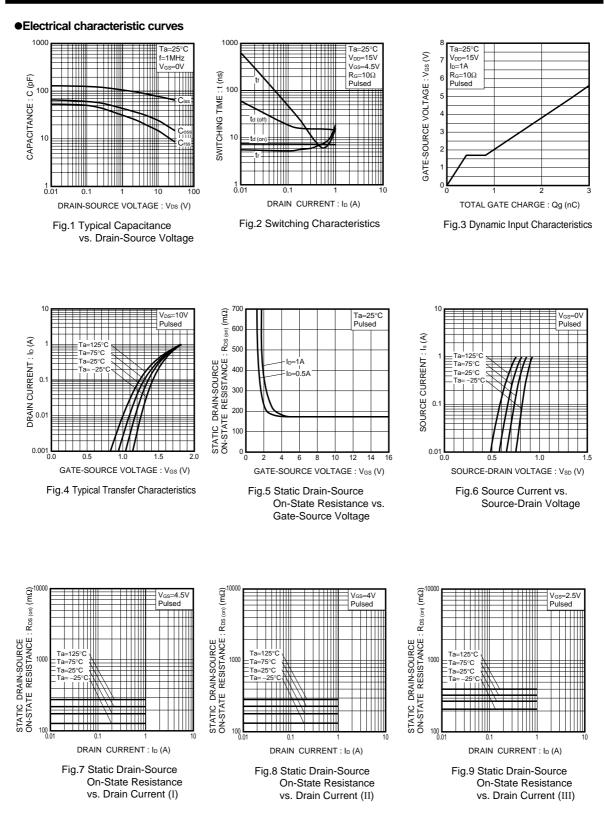
•Body diode characteristics (Source-Drain) (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2>

3.2A, Vgs=0V
3.

QS6K1

Transistors



Rev.B

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